

STRUCTURE AND METHOD OF FORMING A BIPOLAR TRANSISTOR HAVING A VOID BETWEEN EMITTER AND EXTRINSIC BASE

Abstract

Structure and a method are provided for making a bipolar transistor, the bipolar transistor including a collector, an intrinsic base overlying the collector, an emitter overlying the intrinsic base, and an extrinsic base spaced from the emitter by a gap, the gap including at least one of an air gap and a vacuum void.